App No.: Unassigned Docket No.: 204552031400

Inventor: Nobuhiro OHKUBO et al.

Fig.1a

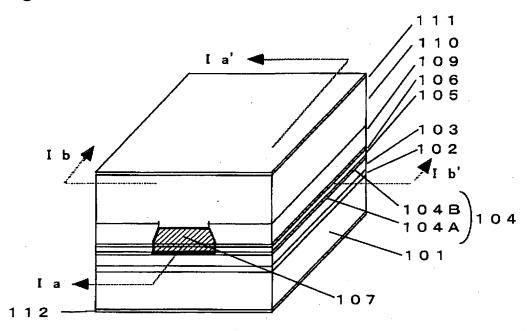


Fig.1b

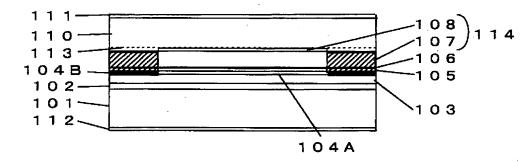
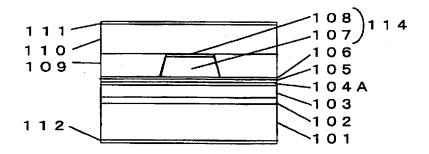


Fig.1c



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Fig.2a

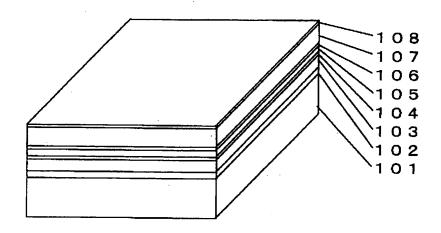


Fig.2b

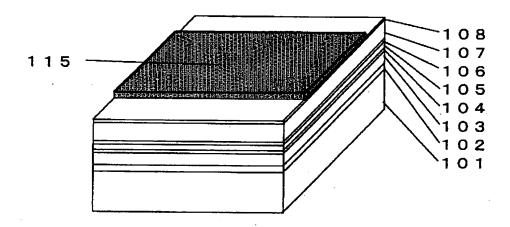
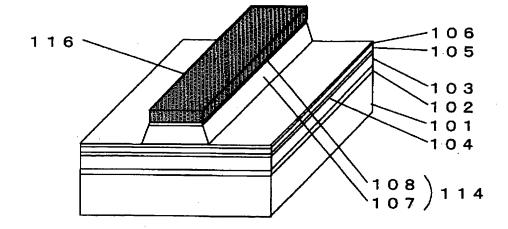


Fig.2c



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Fig.2d

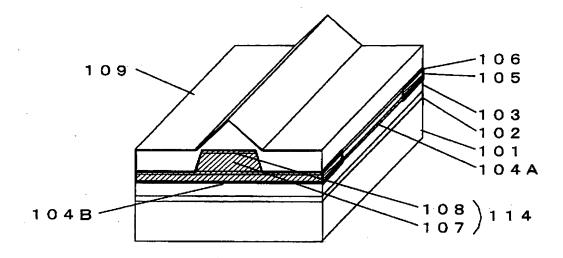


Fig.2e

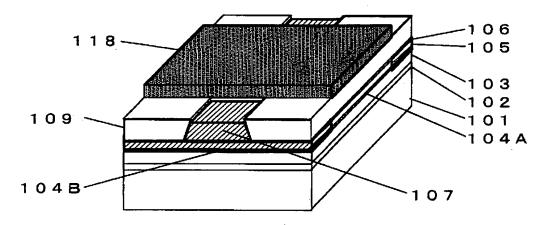
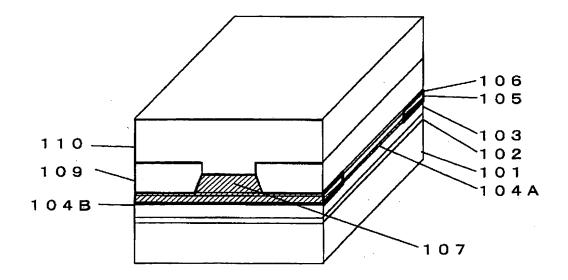


Fig.2f



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Fig.3

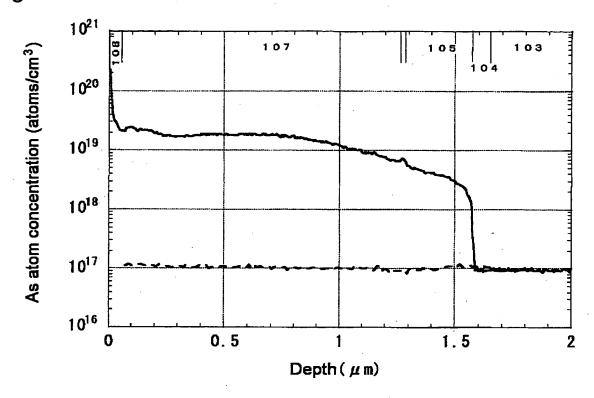
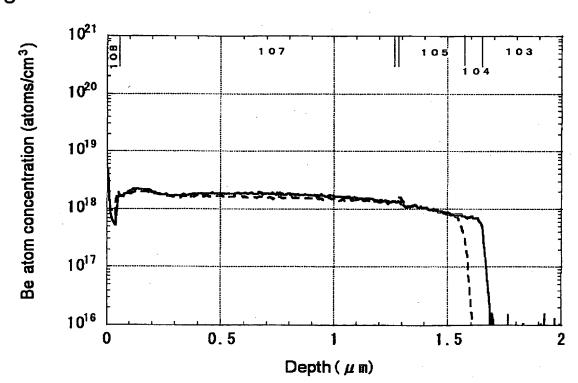
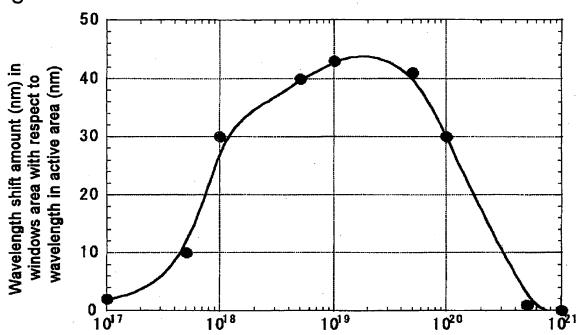


Fig.4



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Fig.5



As atom concentration (cm<sup>-3</sup>) in p-type AlGaInP second clad layer

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Fig.6a

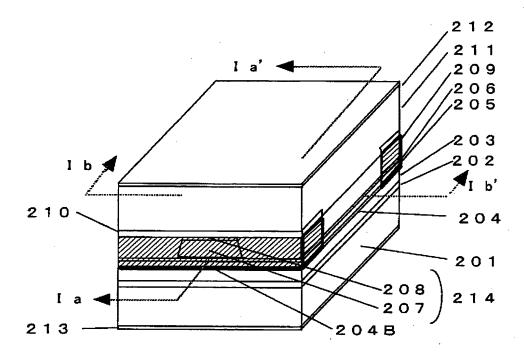


Fig.6b

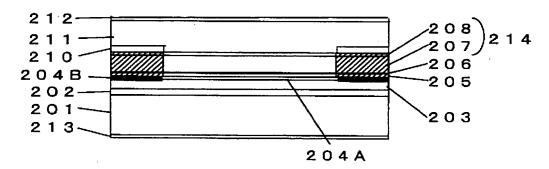
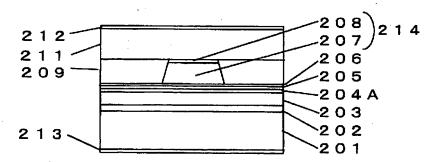


Fig.6c



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Fig.7a

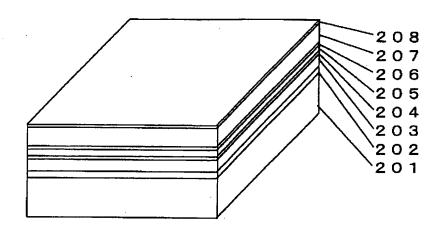


Fig.7b

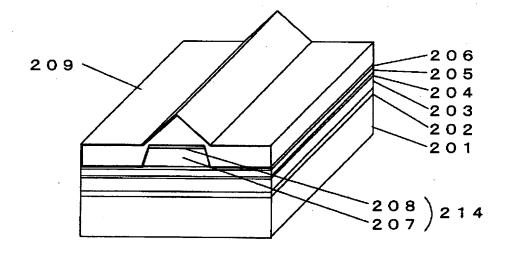
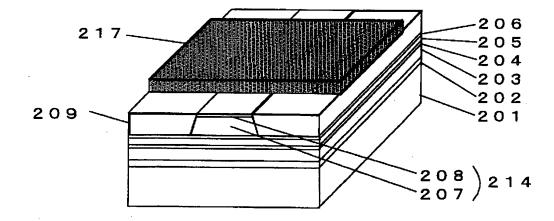


Fig.7c



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Fig.7d

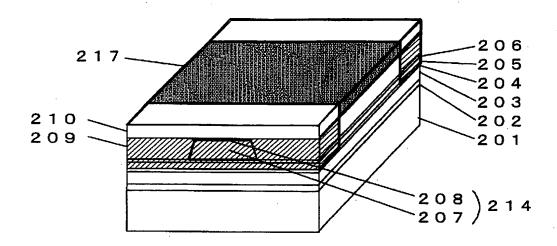
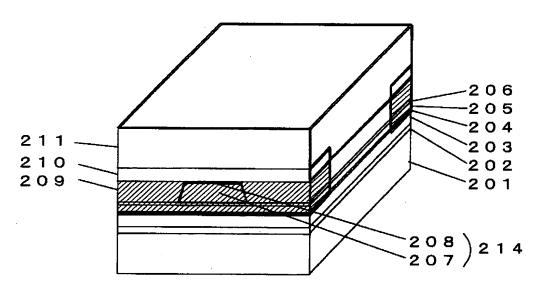


Fig.7e



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Fig.8a

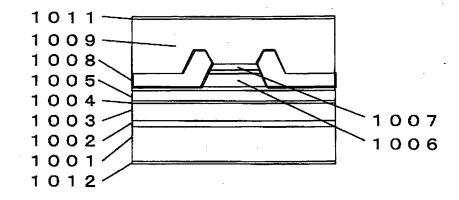


Fig.8b

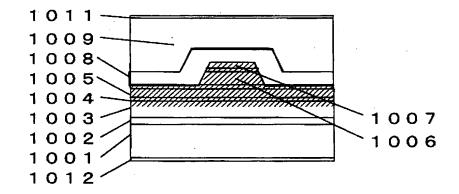
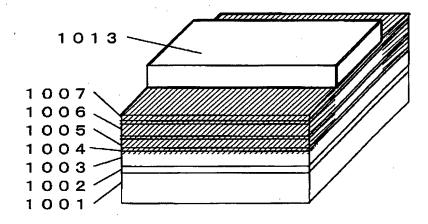


Fig.9a



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Fig.9b

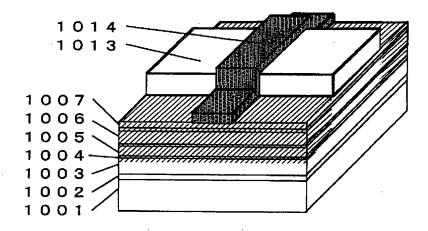


Fig.9c

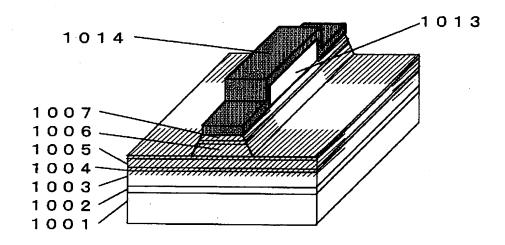


Fig.9d

